Indium Phosphide

Epitaxy Ready Polished Wafers

Wafer Technology offers single crystals that are grown in a pure fused silica system by the Czochralski method from multiple zone refined polycrystalline ingot.

MECHANICAL SPECIFICATIONS

Indium Phosphide can be supplied in as-cut, etched or polished wafer forms. All slices are individually laser scribed with ingot and slice identity to ensure perfect traceability.

ORIENTATION SPECIFICATIONS

Surface orientations are offered to an accuracy of +/- 0.05 degrees using a triple axis X-Ray diffractometer system. Substrates can also be supplied with very precise misorientations in any direction from the growth plane. Higher index substrates of the type (n, 1, 1) where n = 1, 2, 3, 4, 5, 6 etc and orientations such as (110) are also available. We also offer wafers with cleaved flats.

SURFACE SPECIFICATIONS

All wafers are offered with high quality epitaxy-ready finishing. Surfaces are characterised by in-house advanced optical metrology techniques which include Surfscan haze and particle monitoring, spectroscopic ellipsometry and grazing-incidence interferometry.



PACKAGING

Polished Wafers

Coin-style wafer shipper, individually sealed in two outer bags in inert atmosphere. Cassette shipments are available on request.

As-cut Wafers

Cassette shipment. (Glassine bag available on request).

'Process Trial' wafers

Coin-style wafer shipper, individually sealed in one outer bag.

If you do not see the specification you require, please call for details on +44 (0)1908 210444 or email sales@wafertech.co.uk

Wafer Specifications			
Diameter Slices	2"		
Orientation	(100) ± 0.1°		
Diameter (mm)	50.5 ± 0.4		
Flat Option	EJ		
Flat Tolerance	± 0.1°		
Major Flat Length (mm)	16 ± 2		
Minor Flat Length (mm)	8 ± 1		
Thickness (µm)	350 ± 25 or 500 ± 25		

Electrical and Dopant Specifications

Dopant	Туре	Carrier Concentration cm ⁻³	Mobility cm ² V ⁻¹ s ⁻¹	E.P.D. cm ⁻²
Undoped	n-type	≤10 ¹⁶	≥4200	≤5000
Iron	n-type	Semi-Insulating	≥1000	≤5000
Tin	n-type	(7-40) x 10 ¹⁷	2500-750	≤50000
Sulphur	n-type	(1-10) x 10 ¹⁸	2000-1000	≤1000
Zinc	p-type	(1-6) x 10 ¹⁸	Not Specified	≤1000
Low Zinc	p-type	(1-6) x 10 ¹⁷	Not Specified	≤5000

Tighter electrical ranges are available on request.

Flatness Specifications 2 Wafer Form TTV (µm) <12 Polish/Etched Bow (µm) <12

Warp (µm)



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or Polish/Polish



<12